

## SKiiP 362 GDL 060 - 453 WT <sup>12)</sup>

Absolute Maximum Ratings		Values	Units		
Symbol	Conditions <sup>1)</sup>				
<b>IGBT &amp; Inverse Diode</b>					
V <sub>CES</sub>		600	V		
V <sub>CC</sub> <sup>10)</sup>	Operating DC link voltage	400	V		
I <sub>C</sub>	T <sub>heatsink</sub> = 25 °C	300	A		
I <sub>CM</sub>	T <sub>heatsink</sub> = 25 °C, t <sub>p</sub> < 1 ms	600	A		
T <sub>J</sub> <sup>3)</sup>	IGBT & Diode	- 40 ... + 150	°C		
V <sub>isol</sub> <sup>4)</sup>	AC, 1 min.	2500	V		
I <sub>F</sub>	T <sub>heatsink</sub> = 25 °C	300	A		
I <sub>FM</sub>	T <sub>heatsink</sub> = 25 °C; t <sub>p</sub> < 1 ms	600	A		
I <sub>FSM</sub>	t <sub>p</sub> = 10 ms; sin.; T <sub>J</sub> = 150 °C	2160	A		
I <sub>t</sub> (Diode)	t <sub>p</sub> = 10 ms; T <sub>J</sub> = 150 °C	23,4	kA <sup>2</sup> s		
<b>Driver</b>					
V <sub>S1</sub>	Stabilized power supply	18	V		
V <sub>S2</sub> <sup>9)</sup>	Nonstabilized power supply	30	V		
dv/dt	Primary to second. side	75	kV/μs		
T <sub>op</sub> , T <sub>stg</sub>	Operating / stor. temperature	- 25 ... + 85	°C		
<b>Characteristics</b>					
Symbol	Conditions <sup>1)</sup>	min.	typ.	max.	Units
V <sub>(BR)CES</sub>	Driver without power supply	≥ V <sub>CES</sub>	-	-	V
I <sub>CES</sub>	V <sub>GE</sub> = 0 } T <sub>J</sub> = 25 °C	-	0,3	-	mA
	V <sub>CE</sub> = V <sub>CES</sub> } T <sub>J</sub> = 125 °C	-	6	-	mA
V <sub>CESat</sub>	I <sub>C</sub> = 225 A } T <sub>J</sub> = 25 (125) °C	-	2,1(2,0)	-	V
V <sub>CESat</sub>	I <sub>C</sub> = 300 A } T <sub>J</sub> = 25 (125) °C	-	2,3(2,4)	-	V
I <sub>CETRIIP</sub>	T <sub>J</sub> = 125 °C, V <sub>S</sub> = 15 V ± 0,6 V	≥ 375	-	-	A
C <sub>CHC</sub>	per SKiiPPACK AC side	-	0,8	-	nF
L <sub>CE</sub>	Top (Bottom)	-	15	-	nH
t <sub>d(on)</sub>	I <sub>C</sub> = 300 A } V <sub>CC</sub> = T <sub>J</sub> = 125 °C } 300 V inductive load	-	120	-	ns
t <sub>d(on)Driver</sub>		-	1,2	-	μs
t <sub>r</sub>		-	200	-	ns
t <sub>d(off)</sub>		-	0,4	-	μs
t <sub>d(off)Driver</sub>		-	1,2	-	μs
t <sub>f</sub>		-	850	-	ns
E <sub>on</sub> + E <sub>off</sub>	V <sub>CC</sub> = 300 / 400 V	-	50/70	-	mJ
<b>Inverse Diode <sup>2)</sup></b>					
V <sub>F</sub> = V <sub>EC</sub>	I <sub>F</sub> = 225 A } T <sub>J</sub> = 25 (125) °C	-	1,5(1,5)	-	V
	I <sub>F</sub> = 300 A } T <sub>J</sub> = 25 (125) °C	-	1,7(1,7)	-	V
E <sub>on</sub> + E <sub>off</sub>	I <sub>F</sub> = 300 A; T <sub>J</sub> = 125 °C	-	9	-	mJ
<b>IGBT / Inverse Diode <sup>2)</sup></b>					
V <sub>TO</sub>	T <sub>J</sub> = 125 °C	-	0,9/0,74	-	V
r <sub>T</sub>	T <sub>J</sub> = 125 °C	-	5,1/3,3	-	mΩ
<b>Diode <sup>2)</sup> - brake chopper (BC)</b>					
V <sub>F</sub> = V <sub>EC</sub>	I <sub>F</sub> = 225 A } T <sub>J</sub> = 25 (125) °C	-	1,5(1,5)	-	V
	I <sub>F</sub> = 300 A } T <sub>J</sub> = 25 (125) °C	-	1,7(1,7)	-	V
V <sub>TO</sub>	T <sub>J</sub> = 125 °C	-	0,74	-	V
r <sub>T</sub>	T <sub>J</sub> = 125 °C	-	3,3	-	mΩ
<b>Thermal Characteristics</b>					
R <sub>thjh</sub>	per IGBT	-	0,16	-	K/W
R <sub>thjd</sub>	per diode inverter (BC)	-	0,27(0,27)	-	K/W
T <sub>ip</sub> <sup>11)</sup>	Over temperature protection	109	115	121	°C
R <sub>thsa</sub> <sup>6)</sup>	P16/280 / P16/360 <sup>6)</sup>	-	0,036	-	K/W
<b>Mechanical Data</b>					
M <sub>dc</sub>	for DC terminals, SI Units	4	-	6	Nm
M <sub>ac</sub>	for AC terminals, SI Units	8	-	10	Nm
Case			S5		

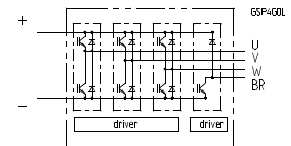
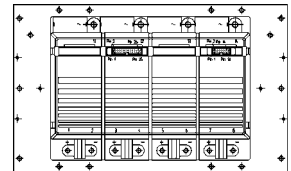
## SKiiPPACK® SK integrated intelligent Power PACK

**3-phase bridge  
with brake chopper**

**SKiiP 362 GDL 060  
+ Driver 453 WT <sup>7)</sup>**

Preliminary Data

Case S5



### Features

- Low thermal impedance
- Optimal thermal management with integrated heatsink
- Pressure contact technology with increased power cycling capability, compact design
- Low stray inductance
- High power, small losses
- Overtemp. protection
- Short circuit protection
- Isolated power supply

<sup>1)</sup> T<sub>heatsink</sub> = 25 °C, unless otherwise specified

<sup>2)</sup> CAL = Controlled Axial Lifetime Technology (soft and fast)

<sup>3)</sup> without driver

<sup>4)</sup> Driver input to DC link/AC output or DC link/AC output to heatsink inverter (other heatsink on request) SKiiPPACK type GD/GDL

<sup>5)</sup> W - Driver wire input

<sup>6)</sup> T - Temperature protection

<sup>7)</sup> 24 V supply voltage selective with SK-DC link (low inductance)

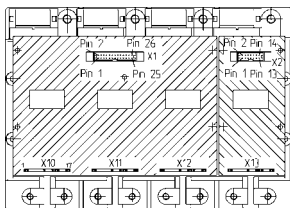
<sup>11)</sup> thermal reference for R<sub>thjh</sub>; R<sub>thsa</sub>

<sup>12)</sup> data for SKiiP362GD060-352WT (IGBT, Inverse diode) identical

**SKiiPACK®**  
**SK integrated**  
**intelligent Power PACK**  
**3-phase bridge with**  
**brake chopper**

**SKiiP 362 GDL 060**  
**+ Driver 453 WT 3)**

Preliminary Driver Data



**Features**

**3-phase bridge**

- CMOS compatible inputs
- Short circuit protection by  $V_{CE}$  monitoring and soft switch off
- Drive interlock top/bottom
- Isolation by transformers
- Supply undervoltage protection
- Overtemperature protection

**Features**

**brake chopper**

- Short circuit protection by  $V_{CE}$  monitoring and soft switch off
- Self controlled switching
- Supply undervoltage protection
- Overtemperature protection

1) 24 V - supply voltage selective

2) Open collector output, external pull-up resistor necessary

3) W - Driver wire input  
 T - Temperature protection

4) Driver data also valid for SKiiP 362GD060 - 352 WT

**SKiiP 362 GDL 060 - 453 WT**

**Driver for 3-phase bridge and brake chopper**

Absolute Maximum Ratings		3-phase bridge <sup>4)</sup>	brake chopper		
Symbol	Conditions	Values		Units	remark
$V_{S1}$	supply voltage primary	18		V	
$V_{S2}^{1)}$	supply voltage primary	30		V	
$I_{outmax}$	output peak current max.	$\pm 10$	$\pm 1,5$	A	
$I_{outAV}$	output average current	$\pm 50$	$\pm 90$	mA	
$f_{swmax}$	switching frequency max.	12	5	kHz	
$V_{CE}$	collector emitter voltage sense across IGBT	600			
dv/dt	rate of rise and fall of voltage (secondary to primary side)	75	50	kV/ $\mu$ s	
$V_{isol IO}$	Isol. test volt. IN/OUT (RMS; 1 min)	2,5		kV~	
$V_{isol 12}$	Isol. test volt. OUT1-OUT2	1,5		kV=	
$T_{op}, T_{stg}$	operating / stor. temperature	-25 ... +85		°C	

**Characteristics**

Symbol	Conditions	Values		Units	remark
$V_{S1}$	supply voltage primary	$15,0 \pm 4\%$		V	
$V_{S2}^{1)}$	supply voltage primary	24,0		V	+25%/-15%
$V_{UVS}$	supply undervolt. monitoring	13		V	
$V_{UVS}^{1)}$	supply undervolt. monitoring	19,5	16	V	
$I_{S01}$	sup.current pr.side (standby)	380	67	mA	
$I_{S02}^{1)}$	sup.current pr.side (standby)	300	67	mA	
$I_{S1}$	sup. current pr.side (max)	900	77	mA	
$I_{S2}^{1)}$	sup. current pr.side (max)	700	77	mA	
$V_{IT+}$	input thresh. volt. (high) min	12,9		V	
$V_{IT-}$	input thresh. volt. (low) max.	2,1		V	
$V_{GE(on)}$	turn-on output gate voltage	15		V	
$V_{GE(off)}$	turn-off output gate voltage	-8	0	V	
$t_{d(on)}$	propagation delay time on	1,2	< 20	$\mu$ s	typ.
$t_{d(off)}$	propagation delay time off	1,2	< 25	$\mu$ s	typ.
$t_{TD}$	dead time of interlock	3		$\mu$ s	typ.
$V_{CEstat}$	VCE-thresh. st. monitoring	3,2		V	typ.
$V_{OL}^{2)}$	logic low output voltage	< 0,6			15 mA sink 2,5mA sink
$V_{oH}^{2)}$	logic high output voltage	max. 30		V	
$V_{RESET L}$	Input voltage RESET Low	< 2		V	
$V_{RESET H}$	Input voltage RESET High	> 12		V	
$V_{iL}$	logic low input volt. Chop. ext. ON	< 5		V	> 5 mA
$V_{iH}$	logic high input volt. Chop. ext. ON	> 11,5		V	< 1 mA
$t_{pdon-error}$	propag. delay time-on error	6	< 60	$\mu$ s	
$t_{p RESET}$	min. pulse width error memory RESET	5		$\mu$ s	
		300		ms	
$T_{err}$	max. temperature	$115 \pm 6$		°C	
$I_{AOmax}$	max. output current	$\pm 5$		mA	pin 20